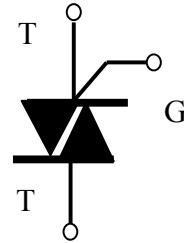


Sensitive Gate Silicon Controlled Rectifiers

■ ■ APPLICATION: High Volume, Line-Powered Consumer Applications.

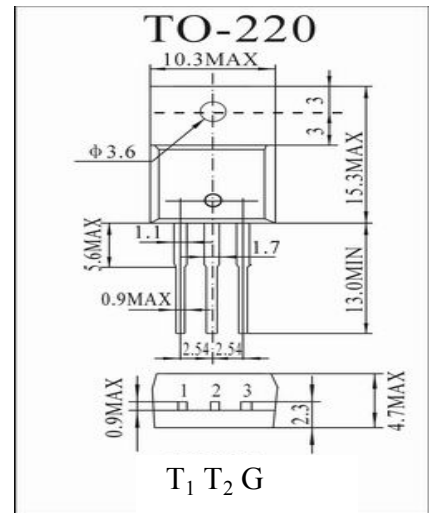
■ ■ FEATURE:

- High Blocking Voltage.
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design.
- Low Peak on State Voltage.



■ ■ MAXIMUM RATINGS (Ta = 25°C unless otherwise noted)

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Peak Repetitive Off State Forward Voltage	V _{DRM}	600	V
Peak Repetitive Off State Reverse Voltage	V _{RRM}	600	V
Forward Average Current	I _{T(AV)}	3	A
Peak Non-Repetitive Surge Current	I _{TSM}	30	A
Forward Peak Gate Power	P _{GM}	1.5	W
Forward Average Gate Power	P _{G(AV)}	0.1	W
Junction Temperature	T _J	125	°C
Storage Temperature Range	T _{stg}	-40~150	°C



■ ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	RATING			UNIT
			MIN.	VALUE	MAX.	
Peak on State Voltage	V _{TM}	I _T =4.5A			1.4	V
Peak Forward Blocking Current	I _{DRM}	V _D =600V			100	uA
Holding Current	I _H			2		mA
Gate Trigger Current (Continuous dc)	I _{GT}	V _{AK} =6V R _L =10Ω			20	mA
						mA
					20	mA
					20	mA
Gate Trigger Voltage (Continuous dc)	V _{GT}	V _{AK} =6V R _L =10Ω			1.5	V
						V
					1.5	V
					1.5	V
Gate Non-Trigger Voltage	V _{GD}	V _D =300V, R _{GK} =1KΩ	0.2			V

■ ■ IGT Classification And Marking

Print Mark	ST603
Classification	
IGT(mA)	